RD50 Discussion on Defects and Materials

- **Notes from last Meeting in June**
  - Mobility values, discrepancies, in low and high fields
  - EPR studies
  - Modeling of V-I in clusters
  - Acceptor removal in p type silicon
  - Donor removal in n-type Si
  - Defect characterization (Wodean on p type)
  - Data base on defects
  - N-enriched project
- **Input from Ioana**
  - Bucharest starting to model the defects that are doing the leakage current
  - Results on EPR attached to the agenda
- **Question from Elena**
  - Should we introduce a new way of labelling of our defects?
- **Remark from Juozas on interpretation of TSC data with different filling**
  - How to deal with this?